

isc N-Channel MOSFET Transistor

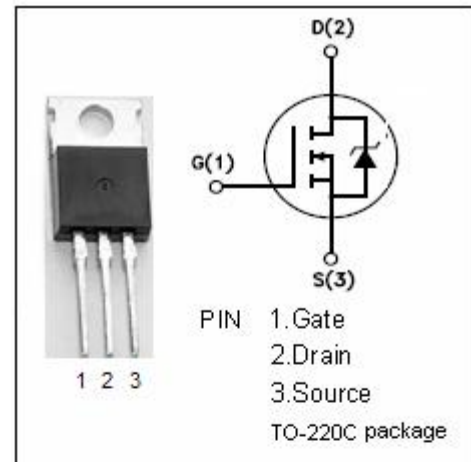
2SK950

DESCRIPTION

- Drain Current $-I_D = 6A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 500V(\text{Min})$

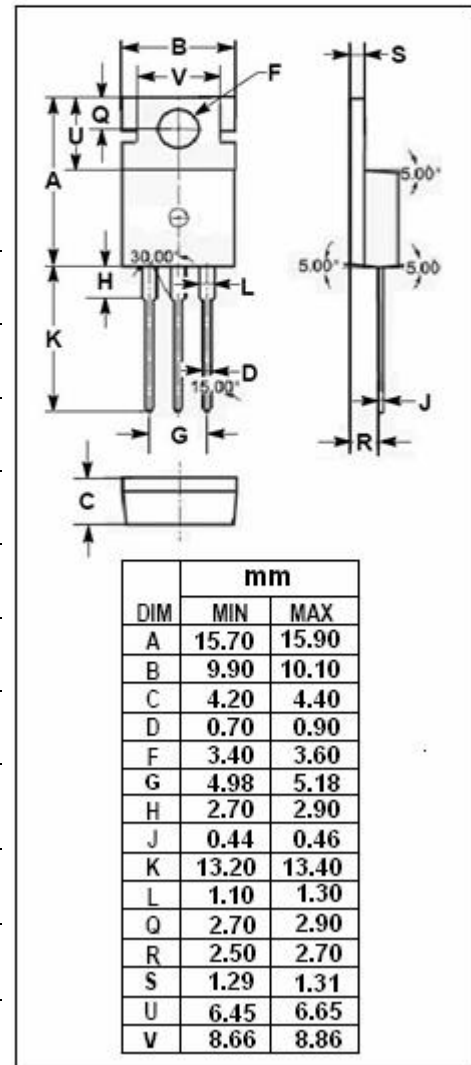
APPLICATIONS

- Designed for high voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.



ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	500	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C = 25^\circ C$	6	A
P_{tot}	Total Dissipation@ $T_C = 25^\circ C$	80	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.56	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	75	$^\circ C/W$

isc N-Channel Mosfet Transistor**2SK950****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	500			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =10mA	2.1	3.0	4.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D = 3.5A		1.0	1.2	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V; V _{GS} = 0			500	uA
V _{SD}	Forward On-Voltage	I _S =6A; V _{GS} =0		1.0	1.5	V
t _r	Rise time	V _{GS} =30V; I _D =2.7A; R _L =50 Ω		40	70	ns
t _{on}	Turn-on time			65	110	ns
t _f	Fall time			60	100	ns
t _{off}	Turn-off time			260	400	ns